

Abstract

A method is proposed for producing semiconductor components, in which at least one doped region is introduced in a wafer, a solid glass layer (2; 4; 2, 3; 4, 5) provided with dopant being applied on at least one of the two sides of a semiconductor wafer (1); in another step, the wafer being heated to high temperatures so that the dopant from the glass layer penetrates deep into the wafer to produce the at least one doped region (10; 11); and in a further step, the glass layer being removed. The method is used for producing homogeneous, heavily doped regions, it also being possible to introduce these regions in the wafer on both sides and for the regions to be of different doping type.

(Figure 1)